

ABSTRACT OF THE DISCLOSURE

A pair of reflective masks is provided in a photolithography process, wherein pattern forming elements are divided into respective direction relative to a projection vector of an EUV ray, so that each of the reflective masks has the same pattern forming elements extending in one direction. The exposure process is sequentially carried out to an object to be exposed using respective reflective mask, and when the reflection mask is changed from one to the other, the object and the other reflective mask are rotated so that the angle of the object and the projection vector becomes the same angle with the reflective mask before it is changed.

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